

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#3

In re Appln. of: Ronald Kakoschke  
 Appln. No.: Not yet assigned  
 Filed: Herewith  
 For: INTEGRATED FIELD-EFFECT  
 TRANSISTOR COMPRISING  
 TWO CONTROL REGIONS,  
 USE OF SAID FIELD-EFFECT  
 TRANSISTOR AND METHOD  
 FOR PRODUCING THE SAME

Examiner: Not yet assigned

Art Unit: N/A

Attorney Docket No: 10808/227

INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following reference(s):

No.	Date of Publication	Patentee/Applicant/Assignee
US2002/0130354 A1	September 19, 2002	Sekigawa et al.
6,369,108 B1	May 28, 2002	Krivokapic et al.
5,930,605	July 27, 1999	Mistry et al.
5,693,918	November 4, 1997	Smith et al.
4,996,574	February 26, 1991	Shirasaki
4,965,213	October 23, 1990	Blake
<b>OTHER ART – NON PATENT LITERATURE DOCUMENTS</b>		
J.M. Hwang, H. Lu, Y.D. Sheu, W. Bailey, P. Mei, G. Pollack, <i>Premature Breakdown in Non-Fully Depleted SOI/Mosfets with Body-Tied-To-Source Structure</i> , pgs. 34-35, SOI Conference, Proceedings. IEEE, October 1, 1991.		
C.J. Chang-Hasnain, J.P. Harbison, C.E. Zah, L.T. Florez and N.C. Andreadakis, <i>Supression of Latch in SOI Mosfits By Silicidation of Source</i> , pgs. 1003-1005, Electronics Letters, Vol. 27, May 23, 1991.		
F.L. Duan and D.E. Ioannou, <i>Design and Analysis of a Novel Mixed Accumulations/Inversion Mode FD SOI Mosfet</i> , pgs. 100-101, Proceedings IEEE International SOI Conference, October 1997.		
S. Cristoloveanu and G. Reichert, <i>Recent Advances in SOI Materials and Device Technologies for High Temperature</i> , pgs. 86-93, High-Temperature Electronics, Materials, Devices and Sensors Conference, IEEE, February 1998.		
Srinath Krishnan, <i>Efficacy of Body Ties Under Dynamic Switching Conditions in Partially Depleted SOI CMOS Technology</i> , pgs. 140-141, IEEE International SOI Conference, 1997.		
Jeffrey W. Sleight, <i>DC and Transient Characterization a Compact Schottky Body Contact Technology for SOI Transistors</i> , pgs. 1451-1456, IEEE Transactions on Electron Devices, July, 1999.		
Copy of International Search Report from corresponding PCT application number PCT/DE03/03131.		
Copy of Examination Report from corresponding PCT application number PCT/DE03/03131.		

JC17 Rec'd PCT/PTO 24 MAR 2005

Applicants are enclosing Form PTO-1449 (one sheet), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary, 37 C.F.R. §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

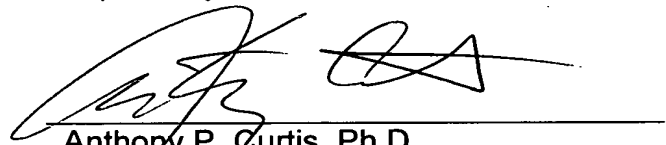
By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

3/24/05

Date

  
Anthony P. Curtis, Ph.D.  
(Reg. No. 46,193)

FORM PTO-1449	SERIAL NO. Not yet assigned	CASE NO. 107929049 10808/227
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE Herewith	GROUP ART UNIT Not yet assigned
APPLICANT(S): Ronald Kakoschke		

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	A1	US2002/0130354 A1	September 19, 2002	Sekigawa et al.		
	A2	6,369,108 B1	May 28, 2002	Krivokapic et al.		
	A3	5,930,605	July 27, 1999	Mistry et al.		
	A4	5,693,918	November 4, 1997	Smith et al.		
	A5	4,996,574	February 26, 1991	Shirasaki		
	A6	4,965,213	October 23, 1990	Blake		

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS <small>(Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)</small>					
	A7	J.M. Hwang, H. Lu, Y.D. Sheu, W. Bailey, P. Mei, G. Pollack, <i>Premature Breakdown in Non-Fully Depleted SOI/Mosfets with Body-Tied-To-Source Structure</i> , pgs. 34-35, SOI Conference, Proceedings. IEEE, October 1, 1991.				
	A8	C.J. Chang-Hasnain, J.P. Harbison, C.E. Zah, L.T. Florez and N.C. Andreadakis, <i>Supression of Latch in SOI Mosfits By Silicidation of Source</i> , pgs. 1003-1005, Electronics Letters, Vol. 27, May 23, 1991.				
	A9	F.L. Duan and D.E. Ioannou, <i>Design and Analysis of a Novel Mixed Accumulations/Inversion Mode FD SOI Mosfet</i> , pgs. 100-101, Proceedings IEEE International SOI Conference, October 1997.				
	A10	S. Cristoloveanu and G. Reichert, <i>Recent Advances in SOI Materials and Device Technologies for High Temperature</i> , pgs. 86-93, High-Temperature Electronics, Materials, Devices and Sensors Conference, IEEE, February 1998.				
	A11	Srinath Krishnan, <i>Efficacy of Body Ties Under Dynamic Switching Conditions in Partially Depleted SOI CMOS Technology</i> , pgs. 140-141, IEEE International SOI Conference, 1997.				
	A12	Jeffrey W. Sleight, <i>DC and Transient Characterization a Compact Schottky Body Contact Technology for SOI Transistors</i> , pgs. 1451-1456, IEEE Transactions on Electron Devices, July, 1999.				
	A13	Copy of International Search Report from corresponding PCT application number PCT/DE03/03131.				
	A14	Copy of Examination Report from corresponding PCT application number PCT/DE03/03131.				

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.